Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	42
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10wleafa-50

○ ROM, RAM capacities

Flash ROM	Data Flash	RAM	RL78/L13	
			64 pins	80 pins
128 KB	4 KB	8 KB[Note]	R5F10WLG	R5F10WMG
96 KB	4 KB	6 KB	R5F10WLF	R5F10WMF
64 KB	4 KB	4 KB	R5F10WLE	R5F10WME
48 KB	4 KB	2 KB	R5F10WLD	R5F10WMD
32 KB	4 KB	1.5 KB	R5F10WLC	R5F10WMC
16 KB	4 KB	1 KB	R5F10WLA	R5F10WMA

Note This is about 7 KB when the self-programming function and data flash function are used. (For details, see **CHAPTER 3** in the RL78/L13 User's Manual.)

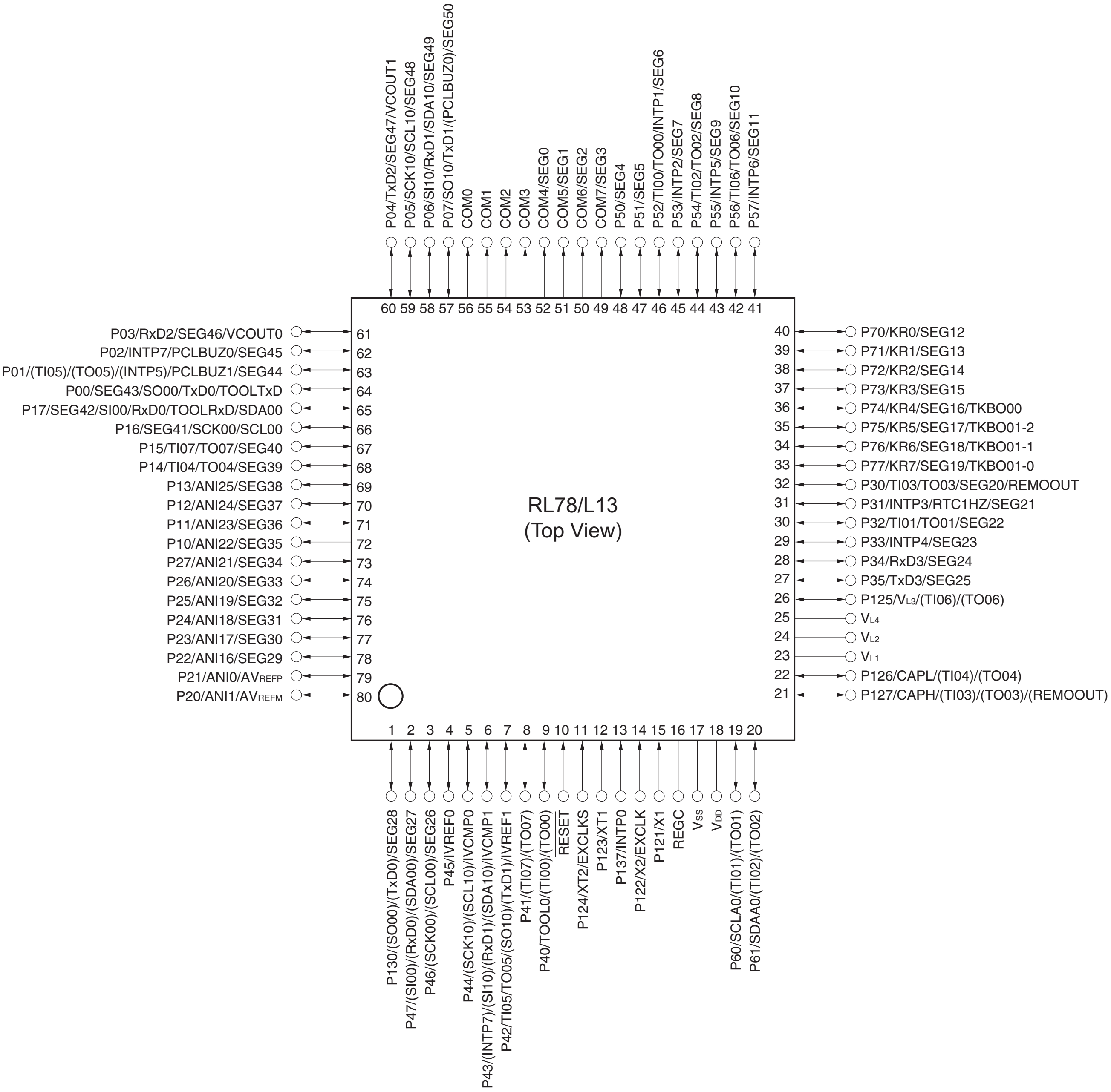
Pin Count	Package	Data Flash	Fields of Application[Note]	Ordering Part Number
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	Mounted	A	R5F10WLAAFA#30, R5F10WLAAFA#50, R5F10WLCAFA#30, R5F10WLCAFA#50, R5F10WLDAFA#30, R5F10WLDAFA#50, R5F10WLEAFA#30, R5F10WLEAFA#50, R5F10WLFAFA#30, R5F10WLFAFA#50, R5F10WLGAFA#30, R5F10WLGAFA#50
	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F10WLAAFB#30, R5F10WLAAFB#50, R5F10WLCAFB#30, R5F10WLCAFB#50, R5F10WLDAFB#30, R5F10WLDAFB#50, R5F10WLEAFB#30, R5F10WLEAFB#50, R5F10WLFAFB#30, R5F10WLFAFB#50, R5F10WLGAFB#30, R5F10WLGAFB#50,
			G	R5F10WLAGFB#30, R5F10WLAGFB#50, R5F10WLCGFB#30, R5F10WLCGFB#50, R5F10WLDGFB#30, R5F10WLDGFB#50, R5F10WLEGFB#30, R5F10WLEGFB#50, R5F10WLFGFB#30, R5F10WLFGFB#50, R5F10WLGGFB#30, R5F10WLGGFB#50
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F10WMAAFA#30, R5F10WMAAFA#50, R5F10WMCAFA#30, R5F10WMCAFA#50, R5F10WMDAFA#30, R5F10WMDAFA#50, R5F10WMEAFA#30, R5F10WMEAFA#50, R5F10WMFAFA#30, R5F10WMFAFA#50, R5F10WMGAFA#30, R5F10WMGAFA#50
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F10WMAAFB#30, R5F10WMAAFB#50, R5F10WMCAFB#30, R5F10WMCAFB#50, R5F10WMDAFB#30, R5F10WMDAFB#50, R5F10WMEAFB#30, R5F10WMEAFB#50, R5F10WMFAFB#30, R5F10WMFAFB#50, R5F10WMGAFB#30, R5F10WMGAFB#50,
			G	R5F10WMAGFB#30, R5F10WMAGFB#50, R5F10WMCGFB#30, R5F10WMCGFB#50, R5F10WMDGFB#30, R5F10WMDGFB#50, R5F10WMEGFB#30, R5F10WMEGFB#50, R5F10WMFGFB#30, R5F10WMFGFB#50, R5F10WMGGFB#30, R5F10WMGGFB#50

Note For the fields of application, see **Figure 1-1 Part Number, Memory Size, and Package of RL78/L13.**

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

<R> 1.3.2 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/L13 User’s Manual.

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1). The current flowing into the LCD controller/driver, 16-bit timer KB20, real-time clock 2, 12-bit interval timer, and watchdog timer is not included.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7\ V \le V_{DD} \le 5.5\ V$@1 MHz to 24 MHz
	$2.4\ V \le V_{DD} \le 5.5\ V$@1 MHz to 16 MHz
LS (low-speed main) mode:	$1.8\ V \le V_{DD} \le 5.5\ V$@1 MHz to 8 MHz
LV (low-voltage main) mode:	$1.6\ V \le V_{DD} \le 5.5\ V$@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

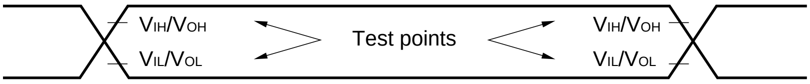
3. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)
(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate[Note 1]		2.4 V≤ V_{DD} ≤ 5.5 V			$f_{MCK}/6$		$f_{MCK}/6$		$f_{MCK}/6$	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		4.0		1.3		0.6	Mbps
		1.8 V ≤ V_{DD} ≤ 5.5 V			–		$f_{MCK}/6$		$f_{MCK}/6$	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		–		1.3		0.6	Mbps
		1.6 V ≤ V_{DD} ≤ 5.5 V			–		–		$f_{MCK}/6$	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		–		–		0.6	Mbps

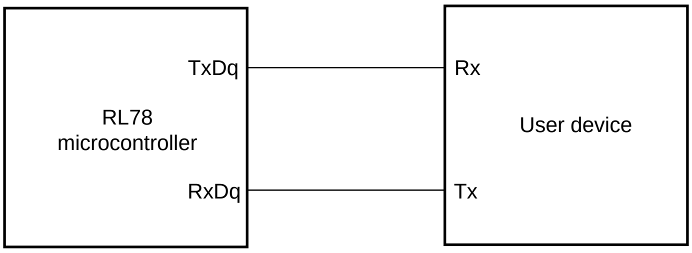
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
	16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			$f_{MCK}/6^{\text{Note 1}}$		$f_{MCK}/6^{\text{Note 1}}$		$f_{MCK}/6^{\text{Note 1}}$	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{\text{Note 3}}$		4.0		1.3		0.6	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			$f_{MCK}/6^{\text{Note 1}}$		$f_{MCK}/6^{\text{Note 1}}$		$f_{MCK}/6^{\text{Note 1}}$	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{\text{Note 3}}$		4.0		1.3		0.6	Mbps
			1.8 V (2.4 $V^{\text{Note 4}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			$f_{MCK}/6$ Note s1, 2		$f_{MCK}/6$ Notes 1, 2		$f_{MCK}/6$ Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{\text{Note 3}}$		4.0		1.3		0.6	Mbps

Notes 1. Transfer rate in SNOOZE mode is 4800 bps only.

2. Use it with V_{DD} ≥ V_b.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
	16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

4. Condition in the HS (high-speed main) mode

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).** For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)
(T_A = –40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ $2/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ – 50		$t_{KCY1}/2$ – 50		$t_{KCY1}/2$ – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ – 120		$t_{KCY1}/2$ – 120		$t_{KCY1}/2$ – 120		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ – 7		$t_{KCY1}/2$ – 50		$t_{KCY1}/2$ – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ – 10		$t_{KCY1}/2$ – 50		$t_{KCY1}/2$ – 50		ns
SIp setup time (to SCKp↑)$^{\text{Note 1}}$	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		ns
SIp hold time (from SCKp↑)$^{\text{Note 1}}$	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↓ to SOp output$^{\text{Note 1}}$	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60		60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130	ns
SIp setup time (to SCKp↓)$^{\text{Note 2}}$	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		110		ns
SIp hold time (from SCKp↓)$^{\text{Note 2}}$	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↑ to SOp output$^{\text{Note 2}}$	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			10		10		10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10		10	ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/2)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		1150		ns
			1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 1.8 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 75$		$t_{KCY1}/2 - 75$		$t_{KCY1}/2 - 75$		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 170$		$t_{KCY1}/2 - 170$		$t_{KCY1}/2 - 170$		ns
		1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 458$		$t_{KCY1}/2 - 458$		$t_{KCY1}/2 - 458$		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 12$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 18$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
		1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
SIp setup time (to SCKp↑)$^{\text{Note 3}}$	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		81		479		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		177		479		479		ns
		1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ		479		479		479		ns
SIp hold time (from SCKp↑)$^{\text{Note 3}}$	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		19		19		19		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		19		19		19		ns
		1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ		19		19		19		ns
Delay time from SCKp↓ to SOp output$^{\text{Note 3}}$	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			100		100		100	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			195		195		195	ns
		1.8 V (2.4 V$^{\text{Note 1}}$) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V$^{\text{Note 2}}$, C_b = 30 pF, R_b = 5.5 kΩ			483		483		483	ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

Notes **1.** Transfer rate in SNOOZE mode: MAX. 1 Mbps

2. Condition in HS (high-speed main) mode

3. Use it with $V_{DD} \geq V_b$.

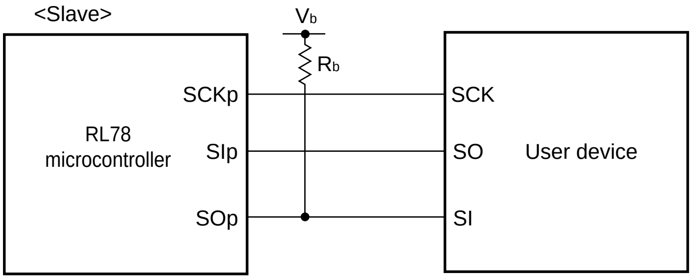
4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

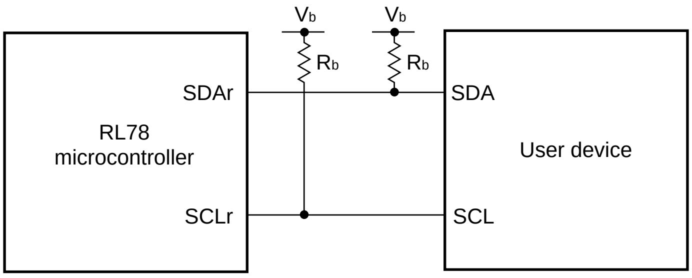
6. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

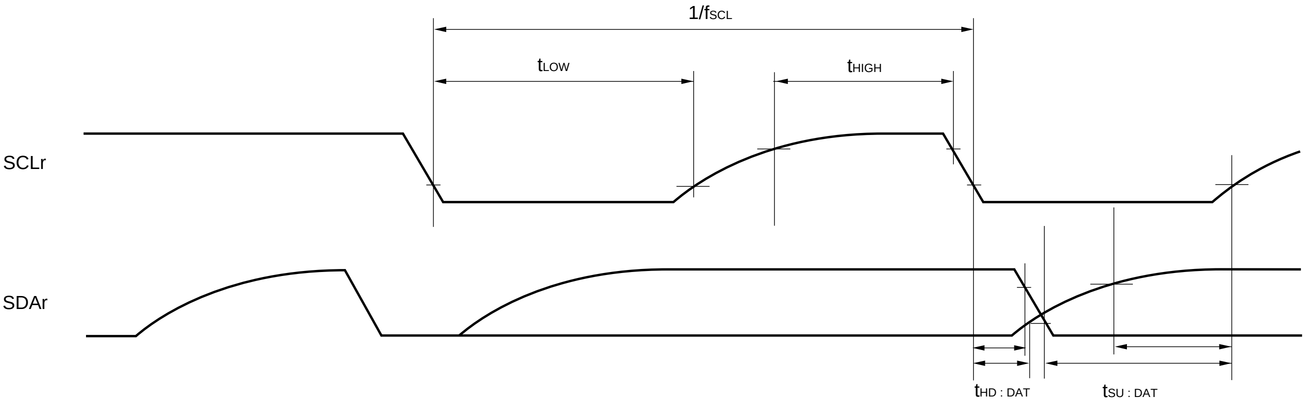
CSI mode connection diagram (during communication at different potential)



Simplified I^2C mode connection diagram (during communication at different potential)



Simplified I^2C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

2. r: IIC number (r = 00, 10), g: PIM, POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 02)

(2) I^2C fast mode

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	2.7 V ≤ V_{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time when SCLA0 ="L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
Hold time when SCLA0 ="H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		100		100		100		ns
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		100		100		100		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V (2.4 V[Note 3]) ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

3. Condition in HS (high-speed main) mode

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

(3) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI0, ANI16 to ANI25

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}[Note 3], Reference voltage (–) = AV_{REFM}[Note 4] = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error[Note 1]	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error [Note 1]	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR}[Note 3]	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.

Zero-scale error:	Add ±0.35%FSR to the AV_{REFM} MAX. value.
Integral linearity error:	Add ±0.5 LSB to the AV_{REFM} MAX. value.
Differential linearity error:	Add ±0.2 LSB to the AV_{REFM} MAX. value.

2.6.2 Temperature sensor /internal reference voltage characteristics

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	ADS register = 80H, T_A = +25°C		1.05		V
Internal reference output voltage	V_{BGR}	ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}				5	μs

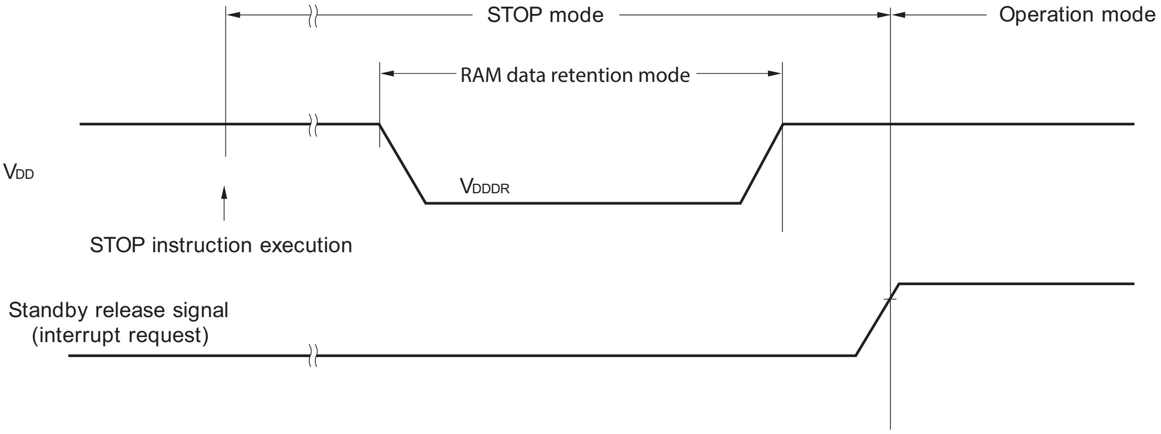
<R> 2.8 RAM Data Retention Characteristics

(T_A = –40 to +85°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46[Note]		5.5	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

<R> **Caution Data in RAM are not retained if the CPU operates outside the specified operating voltage range. Therefore, place the CPU in STOP mode before the operating voltage drops below the specified range.**



2.9 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		24	MHz
Number of code flash rewrites[Notes 1, 2, 3]	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Number of data flash rewrites[Notes 1, 2, 3]		Retained for 1 year T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = –40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = –40 to +105°C
R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB,
R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB
R5F10WMAGFB, R5F10WMCGFB, R5F10WMDGFB,
R5F10WMEGFB, R5F10WMFGFB, R5F10WMGGFB

Cautions 1. The RL78/L13 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L13 User's Manual.

3. Consult Renesas salesperson and distributor for derating when the product is used at T_A = +85°C to +105°C. Note that derating means "systematically lowering the load from the rated value to improve reliability".

<R> **Remark** When RL78/L13 is used in the range of T_A = -40 to +85°C, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (1/3)

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V_{DD}		–0.5 to +6.5	V
REGC pin input voltage	V_{IREGC}	REGC	–0.3 to +2.8 and –0.3 to V_{DD} +0.3^{Note 1}	V
Input voltage	V_{I1}	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	–0.3 to V_{DD} +0.3^{Note 2}	V
	V_{I2}	P60 and P61 (N-ch open-drain)	–0.3 to +6.5	V
	V_{I3}	EXCLK, EXCLKS, $\overline{\text{RESET}}$	–0.3 to V_{DD} +0.3^{Note 2}	V
Output voltage	V_{O1}	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	–0.3 to V_{DD} +0.3^{Note 2}	V
Analog input voltage	V_{AI1}	ANI0, ANI1, ANI16 to ANI26	–0.3 to V_{DD} +0.3 and –0.3 to $AV_{REF(+)}$ +0.3^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF(+)}$: + side reference voltage of the A/D converter.

3. V_{SS}: Reference voltage

Absolute Maximum Ratings (2/3)

Parameter	Symbol	Conditions		Ratings	Unit
LCD voltage	V_{L1}	V_{L1} voltage$^{\text{Note 1}}$		–0.3 to +2.8 and –0.3 to V_{L4} +0.3	V
	V_{L2}	V_{L2} voltage$^{\text{Note 1}}$		–0.3 to V_{L4} +0.3$^{\text{Note 2}}$	V
	V_{L3}	V_{L3} voltage$^{\text{Note 1}}$		–0.3 to V_{L4} +0.3$^{\text{Note 2}}$	V
	V_{L4}	V_{L4} voltage$^{\text{Note 1}}$		–0.3 to +6.5	V
	V_{LCAP}	CAPL, CAPH voltage$^{\text{Note 1}}$		–0.3 to V_{L4} +0.3$^{\text{Note 2}}$	V
	V_{OUT}	COM0 to COM7 SEG0 to SEG50 output voltage	External resistance division method	–0.3 to V_{DD} +0.3$^{\text{Note 2}}$	V
			Capacitor split method	–0.3 to V_{DD} +0.3$^{\text{Note 2}}$	V
			Internal voltage boosting method	–0.3 to V_{L4} +0.3$^{\text{Note 2}}$	V

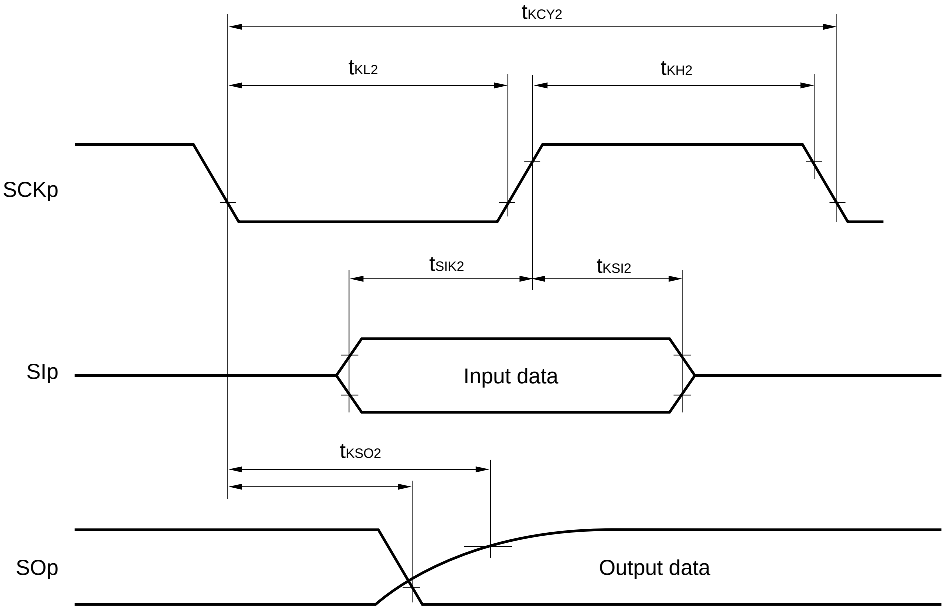
Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 μF ± 30%) and connect a capacitor (0.47 μF ± 30%) between the CAPL and CAPH pins.

2. Must be 6.5 V or lower.

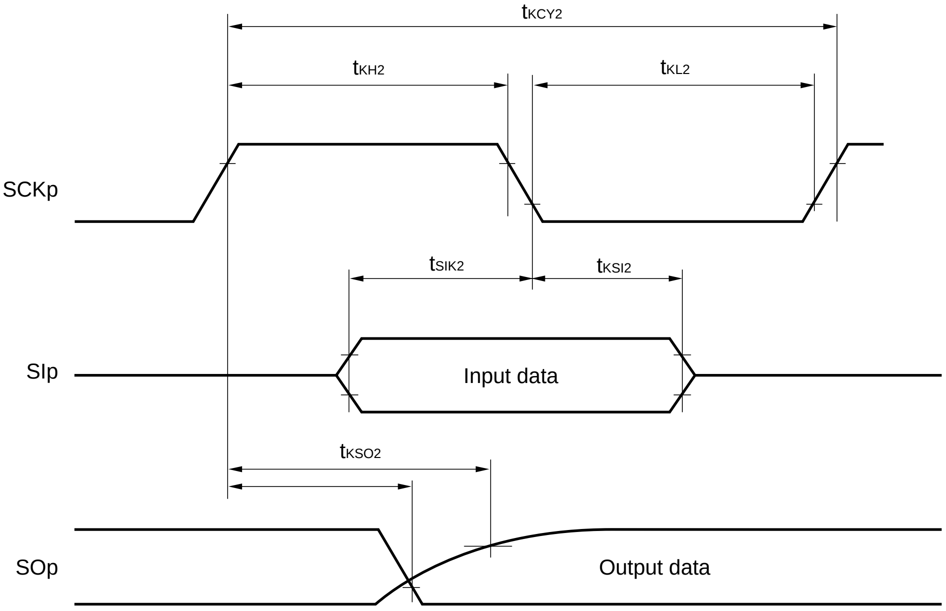
Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark V_{SS}: Reference voltage

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn) m: Unit number, n: Channel number (mn = 00, 02))

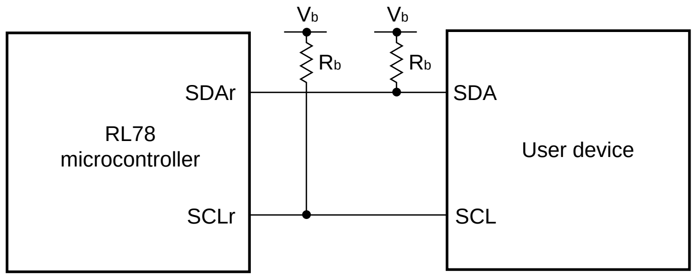
(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^{2}C mode) (1/2)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

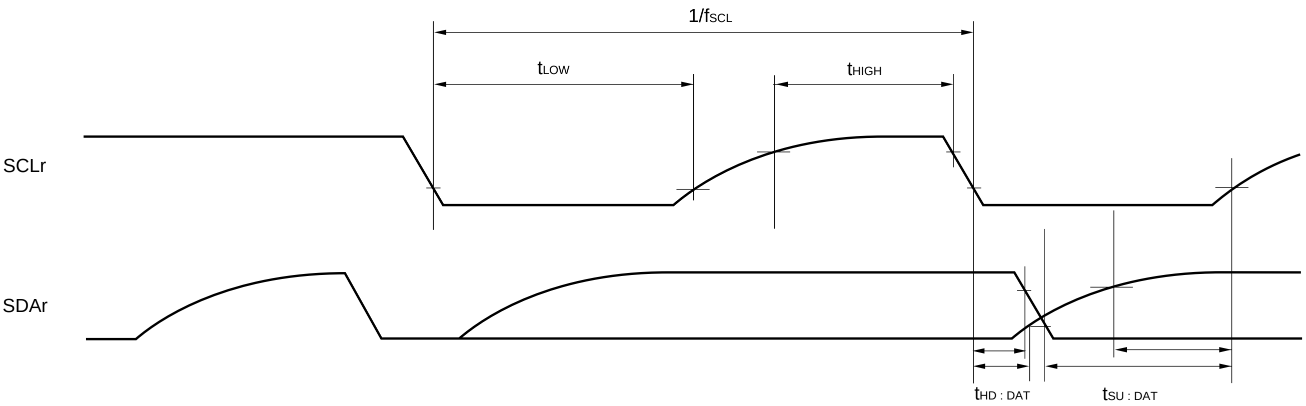
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ		400[Note 1]	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		400[Note 1]	kHz
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		100[Note 1]	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		100[Note 1]	kHz
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ		100[Note 1]	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	4600		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	4600		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	620		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	500		ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	2700		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	2400		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	1830		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



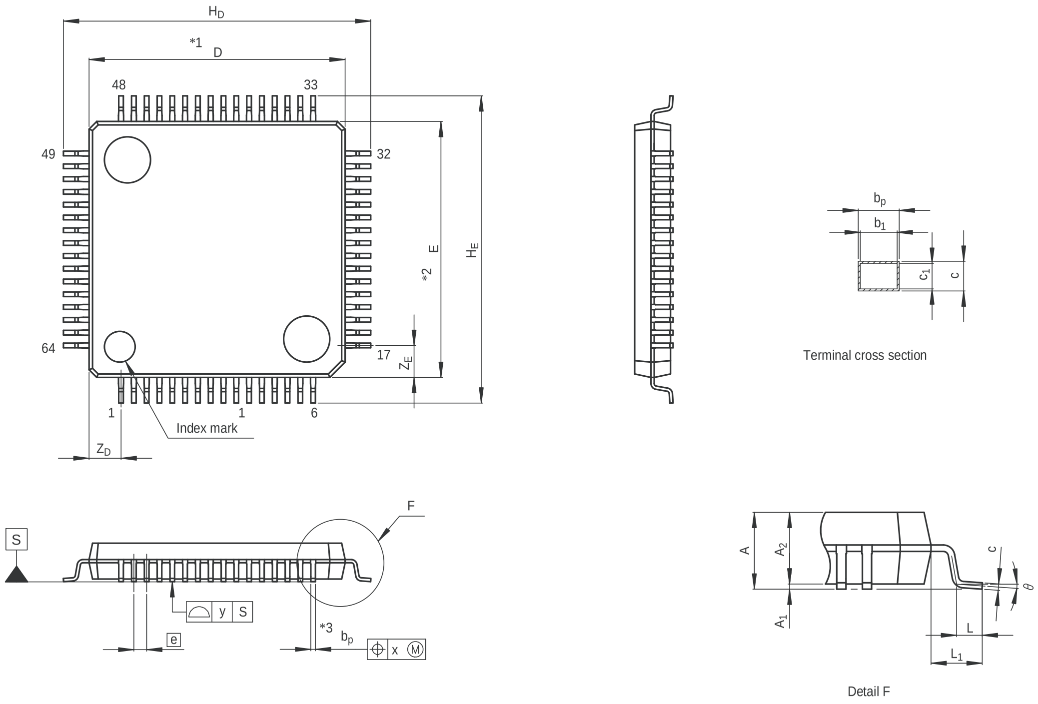
Remarks 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

2. r: IIC number (r = 00, 10), g: PIM, POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02)

R5F10WLAAFB, R5F10WLCAFB, R5F10WLDAFB, R5F10WLEAFB, R5F10WLFAFB, R5F10WLGAFB,
R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB, R5F10WLEGFB, R5F10WLFGFB, R5F10WLGGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP64-10x10-0.50	PLQP0064KB-A	64P6Q-A / FP-64K / FP-64KV	0.3g



Terminal cross section

Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.35	0.5	0.65
L_1	—	1.0	—